

# IRF7314QPbF

HEXFET® Power MOSFET

## Benefits

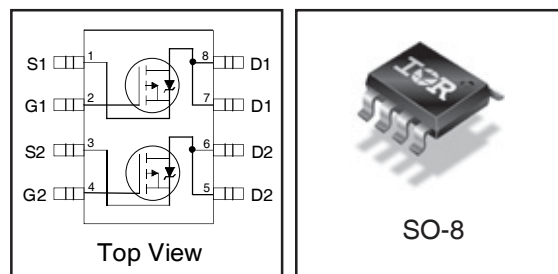
- Advanced Process Technology
- Dual P-Channel MOSFET
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Repetitive Avalanche Allowed up to  $T_{jmax}$
- Lead-Free

## Description

These HEXFET® Power MOSFET's in a Dual SO-8 package utilize the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these HEXFET Power MOSFET's are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.

The 175°C rating for the SO-8 package provides improved thermal performance with increased safe operating area and dual MOSFET die capability make it ideal in a variety of power applications. This dual, surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.

$V_{DSS}$	$R_{DS(on) max}$	$I_D$
-20V	0.058 @ $V_{GS} = -4.5V$	-5.2A
	0.098 @ $V_{GS} = -2.7V$	-4.42A



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-5.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-4.3	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	-43	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation <sup>③</sup>	2.4	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation <sup>③</sup>	1.7	W
	Linear Derating Factor	16	mW/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$E_{AS}$	Single Pulse Avalanche Energy <sup>②</sup>	610	mJ
$I_{AR}$	Avalanche Current <sup>①</sup>	-5.2	A
$E_{AR}$	Repetitive Avalanche Energy	See Fig.14, 15, 16	mJ
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 175	°C

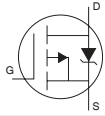
## Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient <sup>③</sup>	62.5	°C/W

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

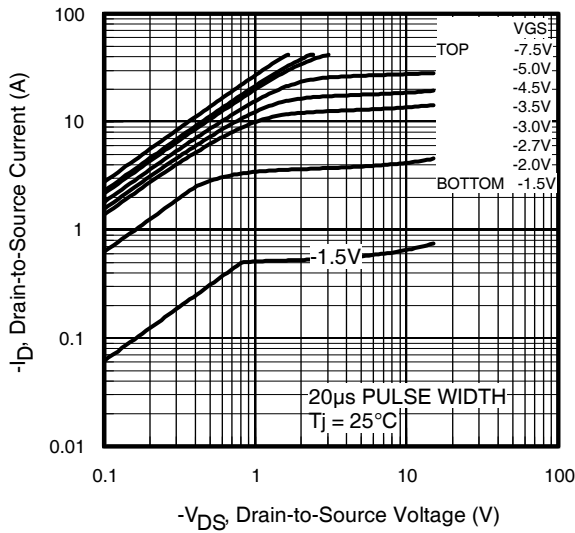
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.009	—	V/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.049	0.058	$\Omega$	$V_{GS} = -4.5V, I_D = -5.2A$ ②
		—	0.082	0.098		$V_{GS} = -2.7V, I_D = -4.42A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.7	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	6.8	—	—	S	$V_{DS} = 10V, I_D = -5.2A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-1.0	$\mu A$	$V_{DS} = -16V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -16V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -12V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 12V$
$Q_g$	Total Gate Charge	—	19	29	nC	$I_D = -5.2A$
$Q_{gs}$	Gate-to-Source Charge	—	2.1	3.2		$V_{DS} = -16V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	9.3	14		$V_{GS} = -4.5V$
$t_{d(on)}$	Turn-On Delay Time	—	18	—	ns	$V_{DD} = -10V$
$t_r$	Rise Time	—	26	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	41	—		$R_G = 6.0\Omega$
$t_f$	Fall Time	—	38	—		$V_{GS} = -4.5V$ ②
$C_{iss}$	Input Capacitance	—	913	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	512	—		$V_{DS} = -15V$
$C_{rss}$	Reverse Transfer Capacitance	—	260	—		$f = 1.0\text{MHz}$

## Source-Drain Ratings and Characteristics

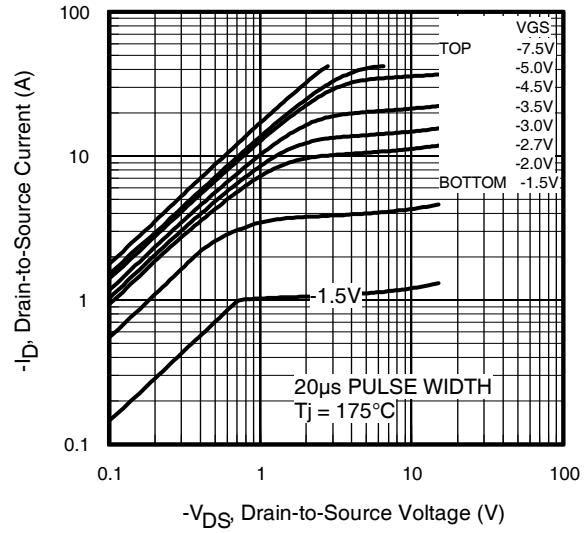
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-3.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-43		
$V_{SD}$	Diode Forward Voltage	—	—	-1.0	V	$T_J = 25^\circ\text{C}, I_S = -3.0A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	44	66	ns	$T_J = 25^\circ\text{C}, I_F = -3.0A$
$Q_{rr}$	Reverse Recovery Charge	—	54	81	nC	$di/dt = -100A/\mu s$ ②

### Notes:

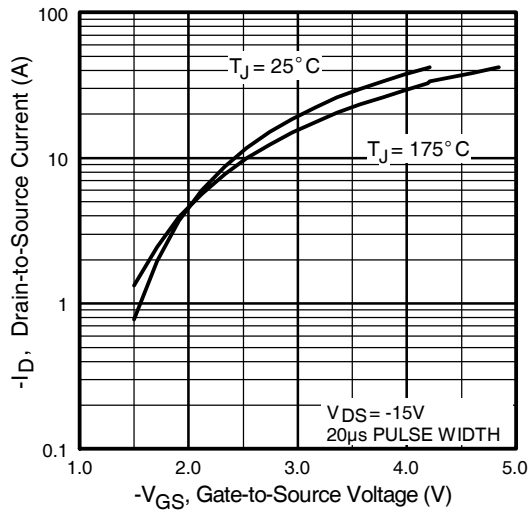
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}, L = 45\text{mH}$   
 $R_G = 25\Omega, I_{AS} = -5.2A$ .
- ③ Surface mounted on FR-4 board,  $t \leq 10\text{sec}$ .
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .



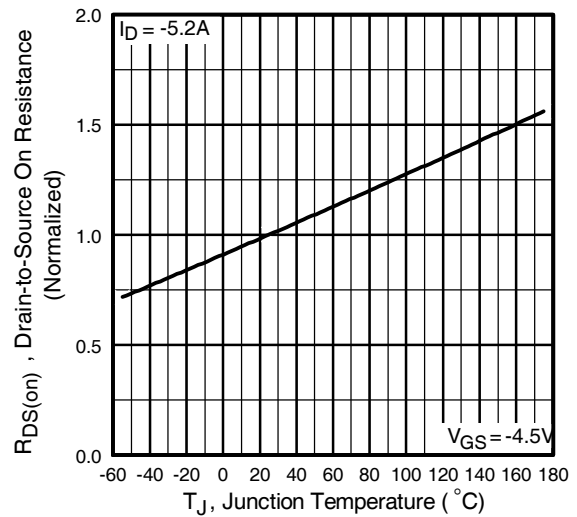
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

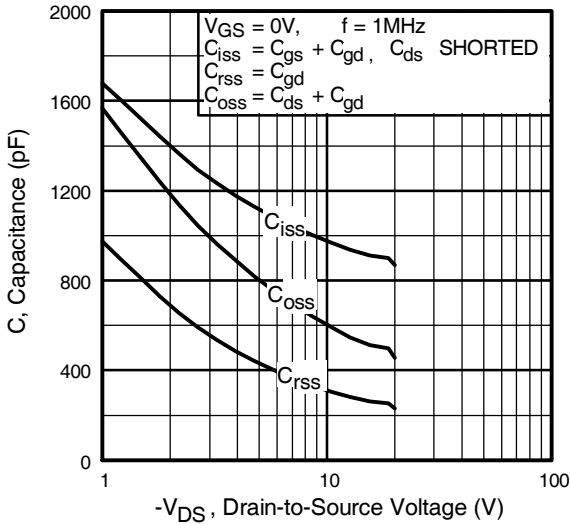


**Fig 3.** Typical Transfer Characteristics

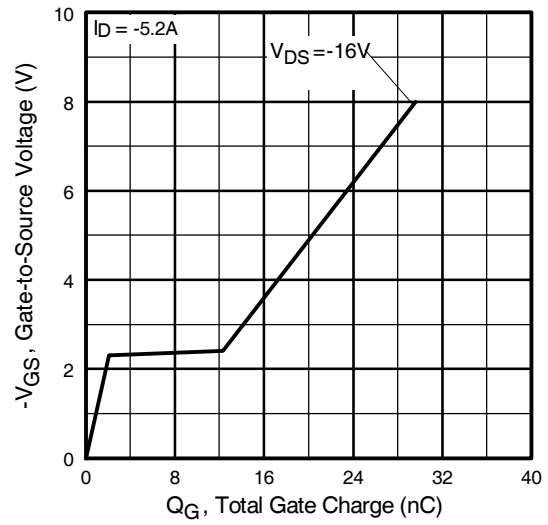


**Fig 4.** Normalized On-Resistance Vs. Temperature

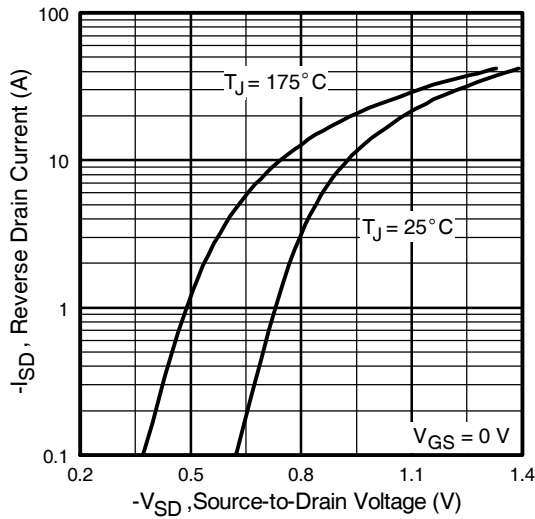
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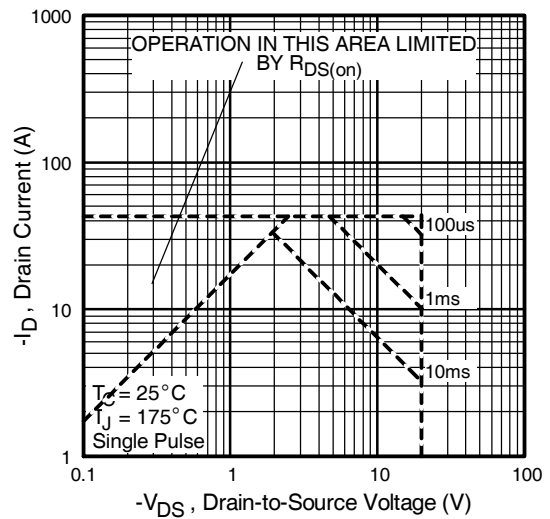
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



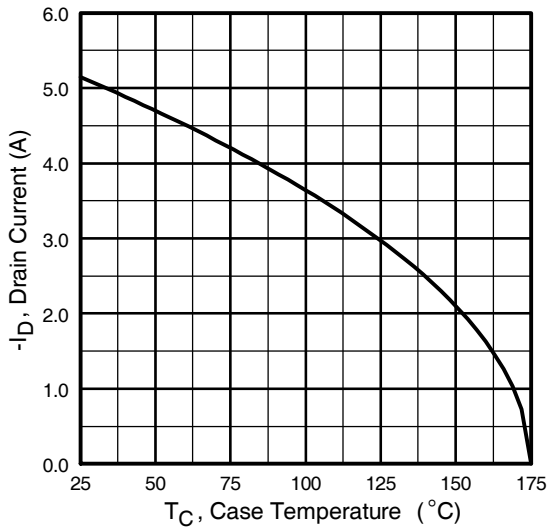
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



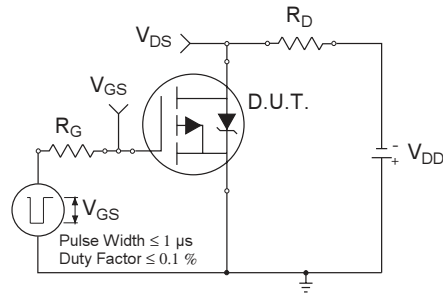
**Fig 7.** Typical Source-Drain Diode Forward Voltage



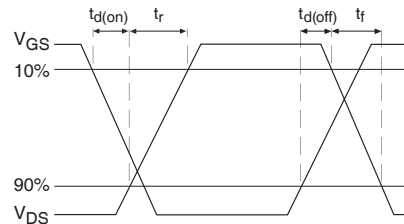
**Fig 8.** Maximum Safe Operating Area



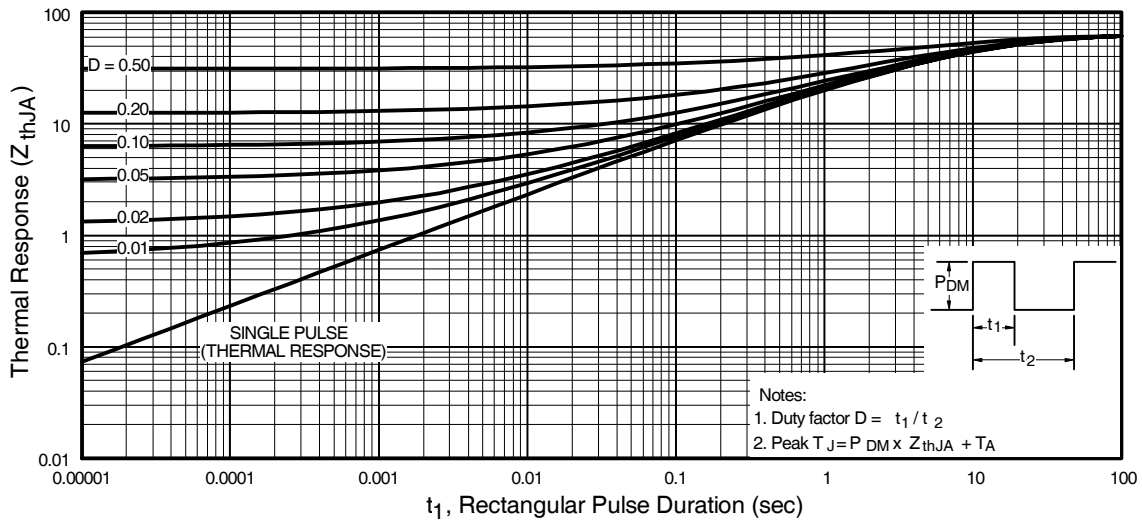
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



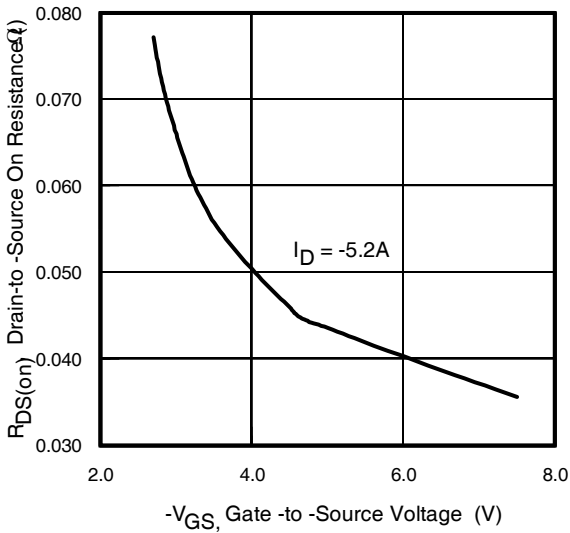
**Fig 10b.** Switching Time Waveforms



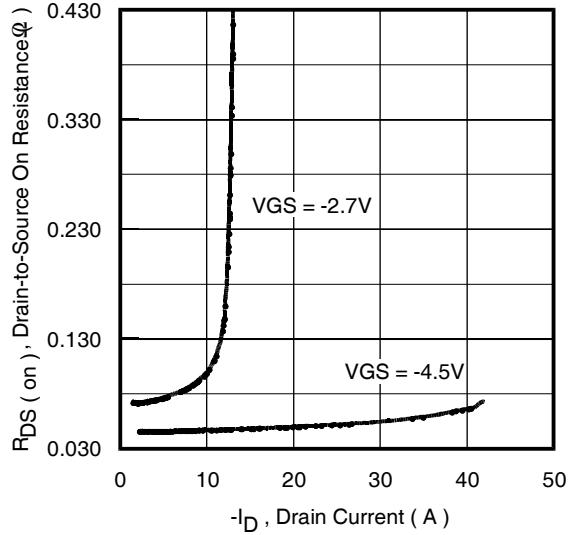
**Fig 10.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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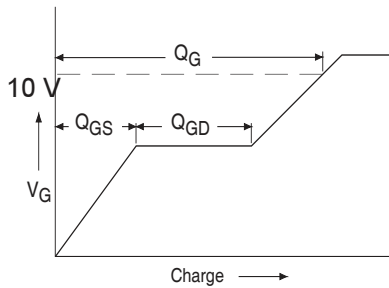
International  
**IR** Rectifier



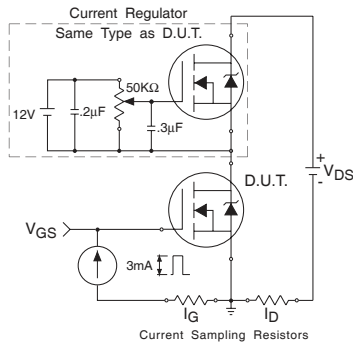
**Fig 11.** Typical On-Resistance Vs. Gate Voltage



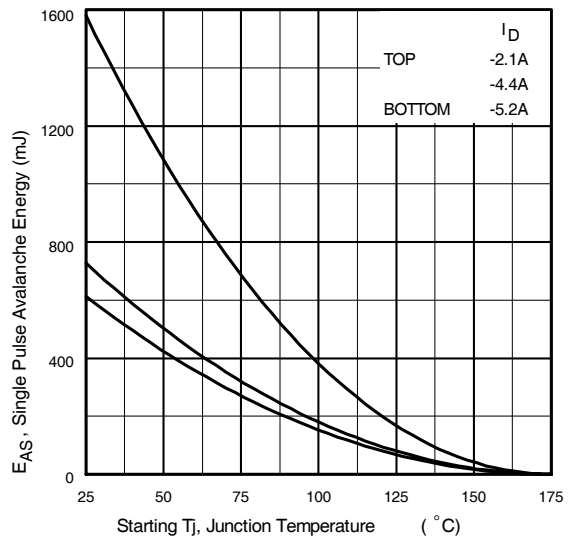
**Fig 12.** Typical On-Resistance Vs. Drain Current



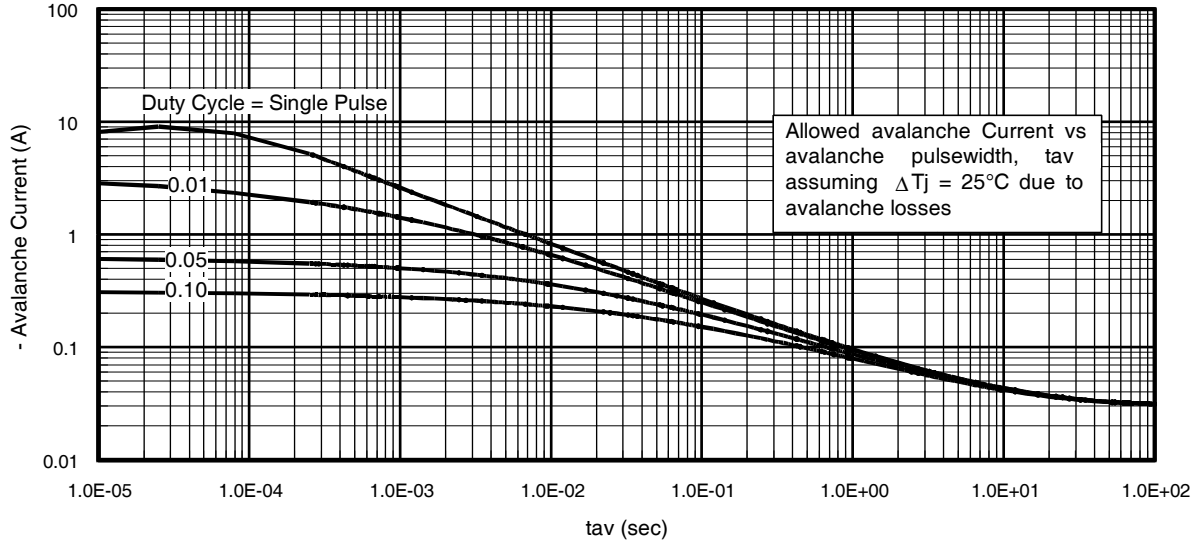
**Fig 13a.** Basic Gate Charge Waveform



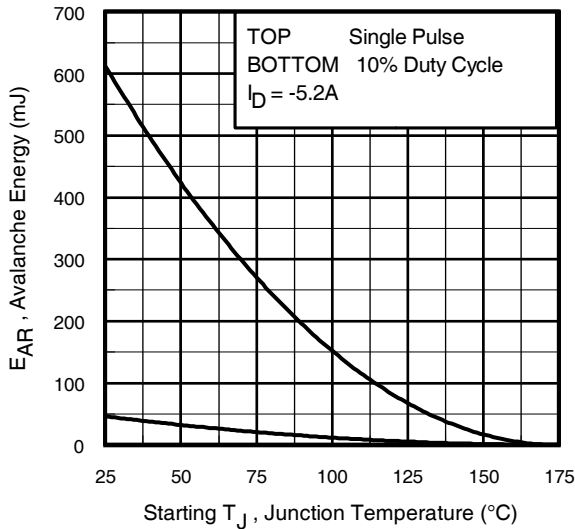
**Fig 13b.** Gate Charge Test Circuit



**Fig 14.** Maximum Avalanche Energy Vs. Drain Current



**Fig 15. Typical Avalanche Current Vs.Pulsewidth**



**Fig 16. Maximum Avalanche Energy Vs. Temperature**

**Notes on Repetitive Avalanche Curves , Figures 15, 16:  
(For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2 \Delta T / [ 1.3 \cdot BV \cdot Z_{th} ]$$

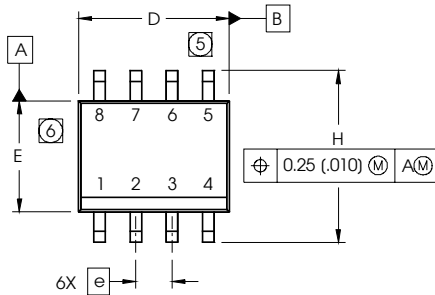
$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

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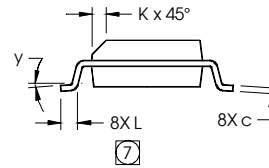
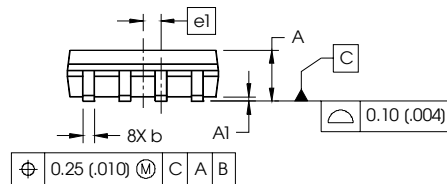
International  
**IR** Rectifier

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)



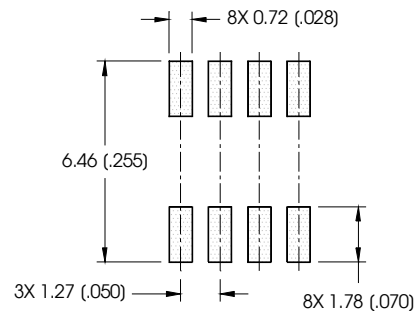
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



### NOTES:

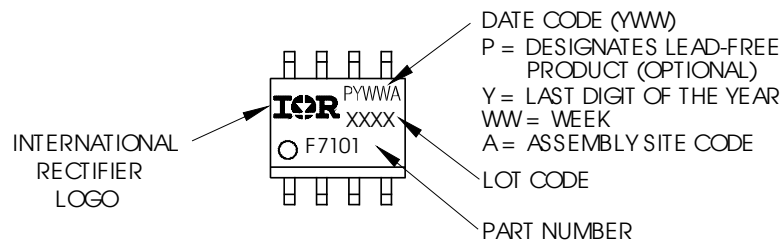
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

### FOOTPRINT



## SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



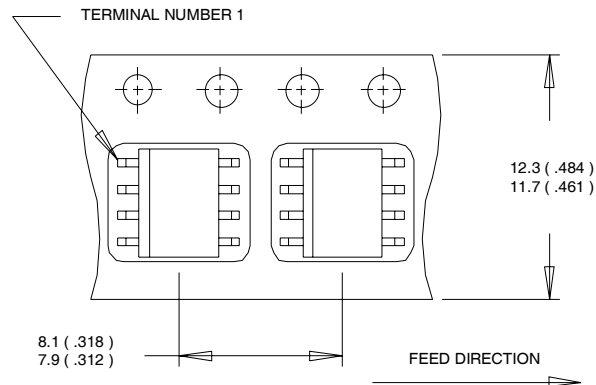
### Notes:

1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>



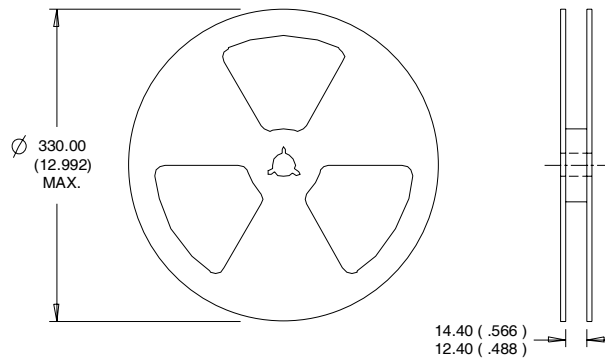
## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



**NOTES:**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualification Standards can be found on IR's Web site.